

2N4401

Preferred Device

General Purpose Transistors

NPN Silicon

Features

- Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V_{CEO}	40	Vdc
Collector – Base Voltage	V_{CBO}	60	Vdc
Emitter – Base Voltage	V_{EBO}	6.0	Vdc
Collector Current – Continuous	I_C	600	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	625 5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5 12	W mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

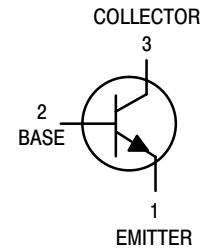
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	$^\circ\text{C}/\text{W}$

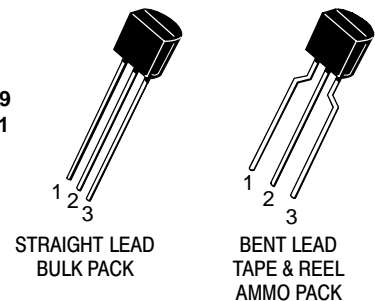
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



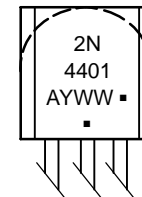
ON Semiconductor®



TO-92
CASE 29
STYLE 1



MARKING DIAGRAM



2N4401 = Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

2N4401

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage (Note 1) ($I_C = 1.0\text{ mAdc}, I_B = 0$)	$V_{(BR)CEO}$	40	–	Vdc
Collector–Base Breakdown Voltage ($I_C = 0.1\text{ mAdc}, I_E = 0$)	$V_{(BR)CBO}$	60	–	Vdc
Emitter–Base Breakdown Voltage ($I_E = 0.1\text{ mAdc}, I_C = 0$)	$V_{(BR)EBO}$	6.0	–	Vdc
Base Cutoff Current ($V_{CE} = 35\text{ Vdc}, V_{EB} = 0.4\text{ Vdc}$)	I_{BEV}	–	0.1	μAdc
Collector Cutoff Current ($V_{CE} = 35\text{ Vdc}, V_{EB} = 0.4\text{ Vdc}$)	I_{CEX}	–	0.1	μAdc

ON CHARACTERISTICS (Note 1)

DC Current Gain ($I_C = 0.1\text{ mAdc}, V_{CE} = 1.0\text{ Vdc}$) ($I_C = 1.0\text{ mAdc}, V_{CE} = 1.0\text{ Vdc}$) ($I_C = 10\text{ mAdc}, V_{CE} = 1.0\text{ Vdc}$) ($I_C = 150\text{ mAdc}, V_{CE} = 1.0\text{ Vdc}$) ($I_C = 500\text{ mAdc}, V_{CE} = 2.0\text{ Vdc}$)	h_{FE}	20 40 80 100 40	– – – 300 –	–
Collector–Emitter Saturation Voltage ($I_C = 150\text{ mAdc}, I_B = 15\text{ mAdc}$) ($I_C = 500\text{ mAdc}, I_B = 50\text{ mAdc}$)	$V_{CE(sat)}$	– –	0.4 0.75	Vdc
Base–Emitter Saturation Voltage ($I_C = 150\text{ mAdc}, I_B = 15\text{ mAdc}$) ($I_C = 500\text{ mAdc}, I_B = 50\text{ mAdc}$)	$V_{BE(sat)}$	0.75 –	0.95 1.2	Vdc

SMALL–SIGNAL CHARACTERISTICS

Current–Gain – Bandwidth Product ($I_C = 20\text{ mAdc}, V_{CE} = 10\text{ Vdc}, f = 100\text{ MHz}$)	f_T	250	–	MHz
Collector–Base Capacitance ($V_{CB} = 5.0\text{ Vdc}, I_E = 0, f = 1.0\text{ MHz}$)	C_{cb}	–	6.5	pF
Emitter–Base Capacitance ($V_{EB} = 0.5\text{ Vdc}, I_C = 0, f = 1.0\text{ MHz}$)	C_{eb}	–	30	pF
Input Impedance ($I_C = 1.0\text{ mAdc}, V_{CE} = 10\text{ Vdc}, f = 1.0\text{ kHz}$)	h_{ie}	1.0	15	k Ω
Voltage Feedback Ratio ($I_C = 1.0\text{ mAdc}, V_{CE} = 10\text{ Vdc}, f = 1.0\text{ kHz}$)	h_{re}	0.1	8.0	$\times 10^{-4}$
Small–Signal Current Gain ($I_C = 1.0\text{ mAdc}, V_{CE} = 10\text{ Vdc}, f = 1.0\text{ kHz}$)	h_{fe}	40	500	–
Output Admittance ($I_C = 1.0\text{ mAdc}, V_{CE} = 10\text{ Vdc}, f = 1.0\text{ kHz}$)	h_{oe}	1.0	30	μmhos

SWITCHING CHARACTERISTICS

Delay Time	$(V_{CC} = 30\text{ Vdc}, V_{BE} = 2.0\text{ Vdc}, I_C = 150\text{ mAdc}, I_{B1} = 15\text{ mAdc})$	t_d	–	15	ns
Rise Time		t_r	–	20	ns
Storage Time	$(V_{CC} = 30\text{ Vdc}, I_C = 150\text{ mAdc}, I_{B1} = I_{B2} = 15\text{ mAdc})$	t_s	–	225	ns
Fall Time		t_f	–	30	ns

1. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

ORDERING INFORMATION

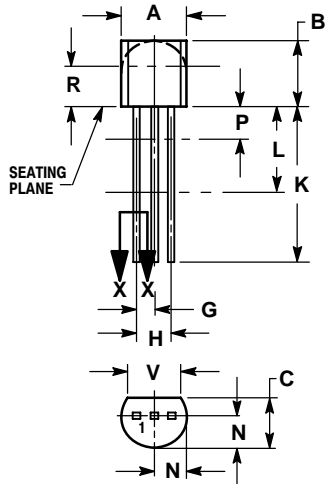
Device	Package	Shipping†
2N4401	TO–92	5000 Units / Bulk
2N4401G	TO–92 (Pb–Free)	5000 Units / Bulk
2N4401RLRA	TO–92	2000 / Tape & Reel
2N4401RLRAG	TO–92 (Pb–Free)	2000 / Tape & Reel
2N4401RLRMG	TO–92 (Pb–Free)	2000 / Ammo Pack
2N4401RLRP	TO–92	2000 / Ammo Pack
2N4401RLRPG	TO–92 (Pb–Free)	2000 / Ammo Pack

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

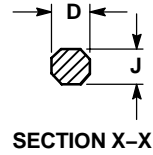
2N4401

PACKAGE DIMENSIONS

TO-92 (TO-226)
CASE 29-11
ISSUE AM



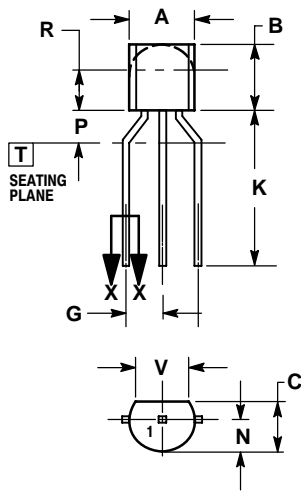
STRAIGHT LEAD
BULK PACK



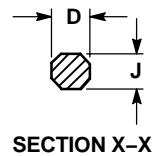
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---



BENT LEAD
TAPE & REEL
AMMO PACK



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	MILLIMETERS	
	MIN	MAX
A	4.45	5.20
B	4.32	5.33
C	3.18	4.19
D	0.40	0.54
G	2.40	2.80
J	0.39	0.50
K	12.70	---
N	2.04	2.66
P	1.50	4.00
R	2.93	---
V	3.43	---

STYLE 1:

1. EMITTER
2. BASE
3. COLLECTOR